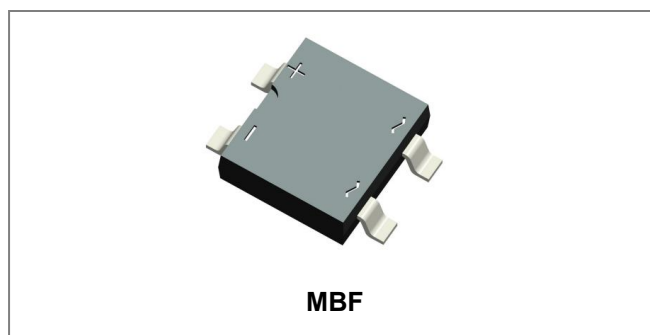


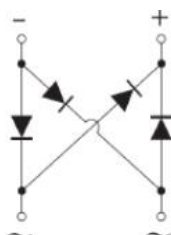
KMB12F THRU KMB125F SINGLE PHASE 1.0 AMP SURFACE MOUNT SCHOTTKY BRIDGE RECTIFIER



Features

- Schottky Barrier Chip
- Low Power Loss, High Efficiency
- Ideally Suited for Automatic Assembly
- Surge Overload Rating to 30A Peak
- Plastic Case Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: MBF, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version

Maximum Ratings:

Type Number	Symbol	KMB 12F	KMB 13F	KMB 14F	KMB 145F	KMB 15F	KMB 16F	KMB 18F	KMB 110F	KMB 115F	KMB 120F	KMB 125F	Unit
Peak Repetitive Reverse Voltage DC Blocking Voltage	V_{RRM} V_{DC}	20	30	40	45	50	60	80	100	150	200	250	V
RMS Voltage	V_{RMS}	14	21	28	31	35	42	56	70	105	140	175	V
Average Rectified Output Current (Note1)@ $T_A=90^{\circ}C$	I_o	1.0											A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30											A
I^2t Rating for fusing ($t < 8.3ms$)	I^2t	5											A ² s

Electrical Characteristics:

Type Number	Symbol	KMB 12F	KMB 13F	KMB 14F	KMB 145F	KMB 15F	KMB 16F	KMB 18F	KMB 110F	KMB 115F	KMB 120F	KMB 125F	Unit	
Forward Voltage (per element) @ $I_F = 1A$	V_F	0.55			0.70		0.85		0.90		0.92		V	
Peak Reverse Current @ $T_A = 25^\circ C$ At Rated DC Blocking Voltage @ $T_A = 100^\circ C$	I_{RM}	0.1						0.05						mA
		10						5						
Typical Junction Capacitance (per leg) (Note 2)	C_J	28											pF	

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Type Number	Symbol	KMB 12F	KMB 13F	KMB 14F	KMB 145F	KMB 15F	KMB 16F	KMB 18F	KMB 110F	KMB 115F	KMB 120F	KMB 125F	Unit
Typical Thermal Resistance (per leg) (Note 3)	$R_{\theta JA}$	75											$^\circ C/W$
Operating junction temperature range	T_J	-55 to +150											$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150											$^\circ C$
Case Style		MB-F											

Note: 1. Mounted on glass epoxy PC board with 1.3mm² solder pad.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
3. Thermal RESistance From Junction to Ambient

Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE

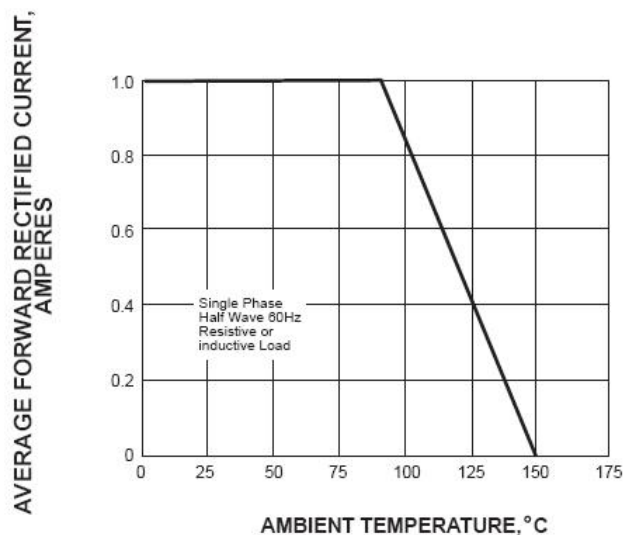
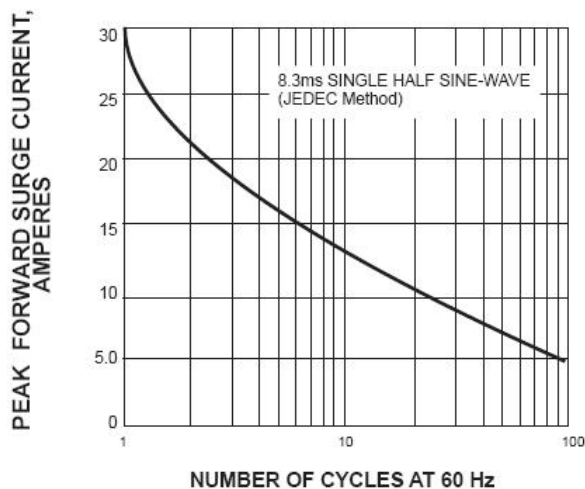
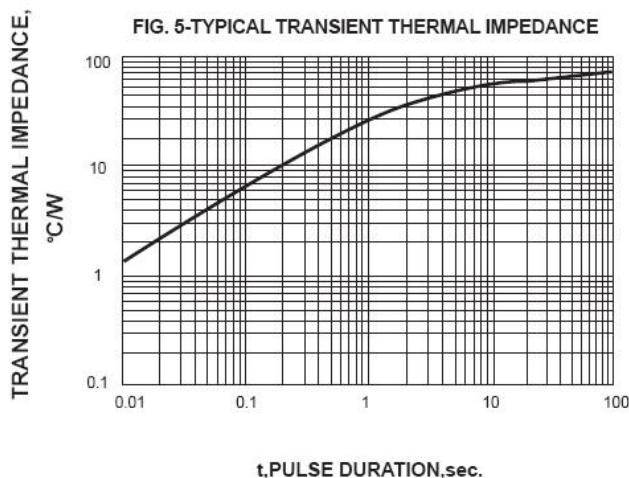
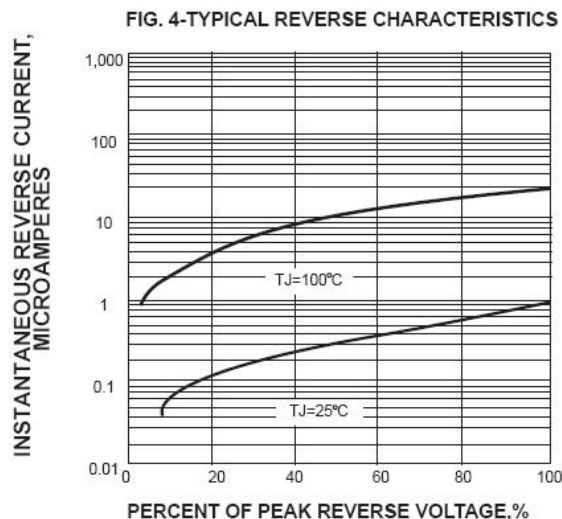
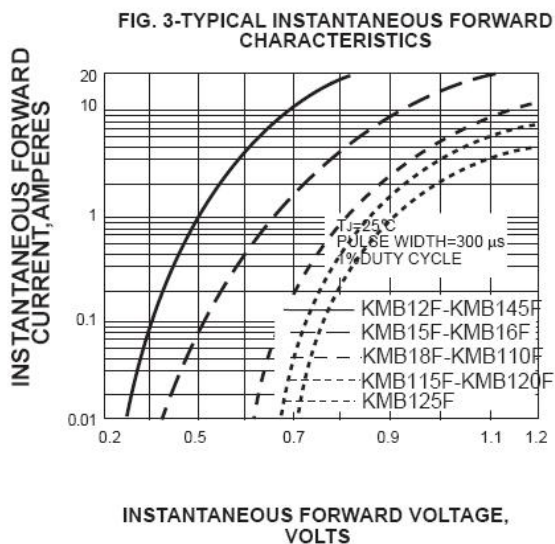


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



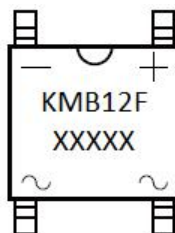


Ordering Information

Device	Package	Shipping
KMB12F THRU KMB125F	MBF (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

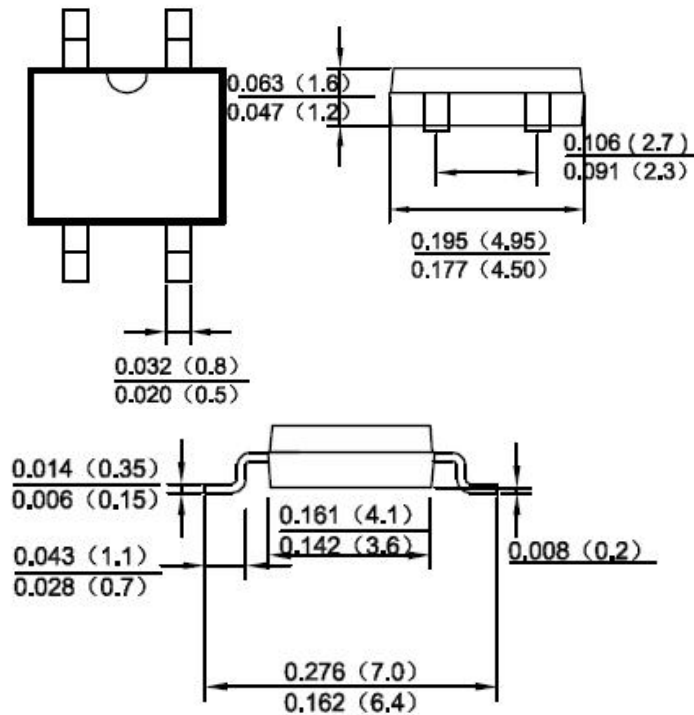


Where XXXXX is YYWWL

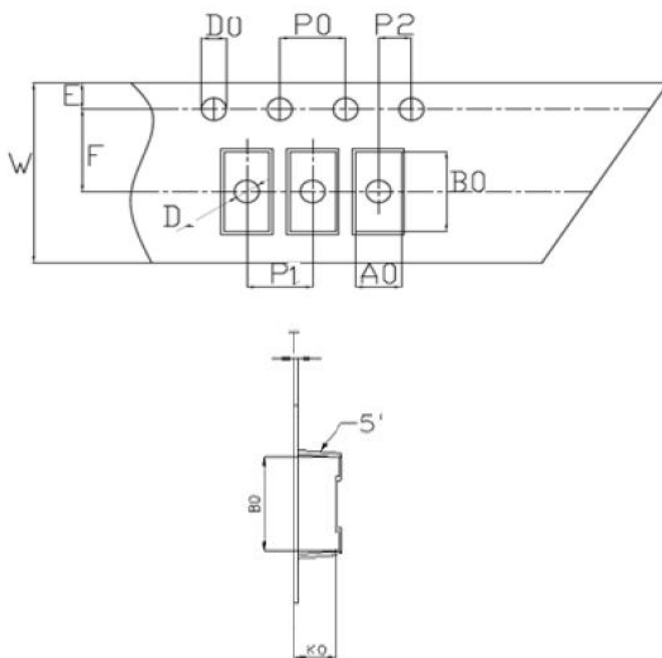
KMB12F = Type Number
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Mechanical Dimensions MBF(Inches/Millimeters)



Carrier Tape & Reel Specification MBF



SYMBOL	Millimeters	
	Min.	Max.
A0	5.21	5.41
B0	7.10	7.30
D0	1.50	1.60
D1	1.40	1.60
P0	3.90	4.10
P1	7.90	8.10
P2	1.95	2.05
E	1.65	1.85
K0	1.55	1.75
F	5.45	5.55
W	11.90	12.10
T	0.24	0.30
10P0	39.80	40.20

**Technical Data
Data Sheet N1777, Rev. A**



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